MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS E6

650V CoolMOS™ E6 Power Transistor
IPx65R600E6

Never stop thinking

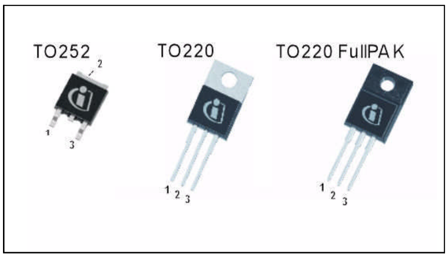
Data Sheet

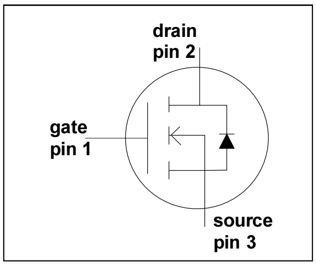
Rev. 2.0, 2010-07-15
Final

Industrial & Multimarket

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ E6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler.





Features

- Extremely low losses due to very low FOM R_{dson}*Q_g and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- JEDEC[1] qualified, Pb-free plating, Halogen free[2]

Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	700	V
$R_{DS(on),max}$	0.6	Ω
$Q_{g,typ}$	23	nC
$I_{D,pulse}$	18	A
E_{oss} @ 400V	2	µJ
Body diode di/dt	500	A/µs

Type / Ordering Code	Package	Marking	Related Links
IPD65R600E6	PG-TO252	65E6600	IFX CoolMOS Webpage
IPP65R600E6	PG-TO220		IFX Design tools
IPA65R600E6	PG-TO220 FullPAK		

1) J-STD20 and JESD22
2) no PG-To252

Table of Contents

2 Maximum ratings

at T_j = 25 °C, unless otherwise specified.

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current1)	I_D	-	-	7.3	A	T_C= 25 °C
				4.6		T_C= 100°C
Pulsed drain current2)	$I_{D,pulse}$	-	-	18	A	T_C=25 °C
Avalanche energy, single pulse	E_{AS}	-	-	142	mJ	I_D=1.3 A, V_{DD}=50 V (see table 21)
Avalanche energy, repetitive	E_{AR}	-	-	0.21		I_D=1.3 A, V_{DD}=50 V
Avalanche current, repetitive	I_{AR}	-	-	1.3	A	
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	V_{DS}=0...480 V
Gate source voltage	V_{GS}	-20	-	20	V	static
		-30		30		AC (f>1 Hz)
Power dissipation for Non FullPAK	P_{tot}	-	-	63	W	T_C=25 °C
Power dissipation for FullPAK	P_{tot}	-	-	28	W	T_C=25 °C
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	
Mounting torque TO-220		-	-	60	Ncm	M3 and M3.5 screws
Mounting torque TO-220 FullPAK				50		M2.5 screws
Continuous diode forward current	I_S	-	-	6.3	A	T_C=25 °C
Diode pulse current2)	$I_{S,pulse}$	-	-	18	A	T_C=25 °C
Reverse diode dv/dt3)	dv/dt	-	-	15	V/ns	V_{DS}=0...480 V, $I_{SD} \leq I_D$, T_j=125 °C (see table 22)
Maximum diode commutation speed3)	di_f/dt			500	A/µs	

1) Limited by $T_{j,max.}$ Maximum duty cycle D=0.75
2) Pulse width t_p limited by $T_{j,max}$
3) Identical low side and high side switch with identical R_G

3 Thermal characteristics

Table 3 Thermal characteristics TO-220 (IPP65R600E6)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	2.0	°C/W	
Thermal resistance, junction - ambient	R_{thJA}	-	-	62		leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

Table 4 Thermal characteristics TO-220FullPAK (IPA65R600E6)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	4.5	°C/W	
Thermal resistance, junction - ambient	R_{thJA}	-	-	80		leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

Table 5 Thermal characteristics TO-252 (IPD65R600E6)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	2.0	°C/W	
Thermal resistance, junction - ambient	R_{thJA}	-	-	62		SMD version, device on PCB, minimal footprint
			35			SMD version, device on PCB, 6cm^2 cooling area[1)]
Soldering temperature, wave- & reflowsoldering allowed	T_{sold}	-	-	260	°C	reflow MSL1

1) Device on 40mm*40mm*1.5 epoxy PCB FR4 with 6cm^2 (one layer, 70µm thick) copper area for drain connection. PCB is vertical without air stream cooling.

4 Electrical characteristics

Electrical characteristics, at Tj=25 °C, unless otherwise specified

Table 6 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	V_{GS}=0 V, I_D=1.0 mA
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5		V_{DS}=V_{GS}, I_D=0.21 mA
Zero gate voltage drain current	I_{DSS}	-	-	1	µA	V_{DS}=600 V, V_{GS}=0 V, T_j=25 °C
		-	10	-		V_{DS}=600 V, V_{GS}=0 V, T_j=150 °C
Gate-source leakage current	I_{GSS}	-	-	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	-	0.54	0.6	Ω	V_{GS}=10 V, I_D=2.1 A, T_j=25 °C
		-	1.40	-		V_{GS}=10 V, I_D=2.1 A, T_j=150 °C
Gate resistance	R_G	-	10.5	-	Ω	f=1 MHz, open drain

Table 7 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	440	-	pF	V_{GS}=0 V, V_{DS}=100 V, f=1 MHz
Output capacitance	C_{oss}	-	30	-		
Effective output capacitance, energy related[1)]	$C_{o(er)}$	-	21	-		V_{GS}=0 V, V_{DS}=0...480 V
Effective output capacitance, time related[2)]	$C_{o(tr)}$	-	88	-		I_D=constant, V_{GS}=0 V V_{DS}=0...480V
Turn-on delay time	$t_{d(on)}$	-	10	-	ns	V_{DD}=400 V, V_{GS}=13 V, I_D=3.2A, R_G= 6.8 Ω (see table 20)
Rise time	t_r	-	8	-		
Turn-off delay time	$t_{d(off)}$	-	64	-		
Fall time	t_f	-	11	-		

1) $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$
2) $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

Table 8 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
IGate to source charge	Q_{gs}	-	2.75	-	nC	V_{DD}=480 V, I_D=3.2 A, V_{GS}=0 to 10 V
Gate to drain charge	Q_{gd}	-	12	-		
Gate charge total	Q_g	-	23	-		
Gate plateau voltage	$V_{plateau}$	-	5.5	-	V	

Table 9 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	V_{GS}=0 V, I_F=3.2A, T_j=25 °C
Reverse recovery time	t_{rr}	-	270	-	ns	V_R=400 V, I_F=3.2 A, di_F/dt=100 A/µs (see table 22)
Reverse recovery charge	Q_{rr}	-	2.0	-	µC	
Peak reverse recovery current	I_{rrm}	-	13	-	A	

5 Electrical characteristics diagrams

Table 10

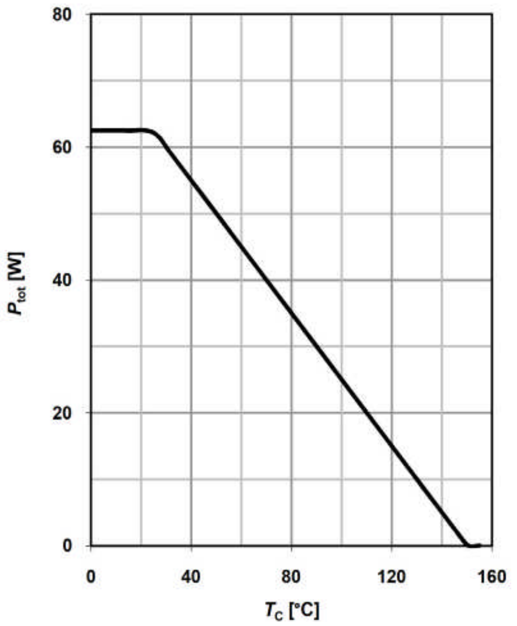
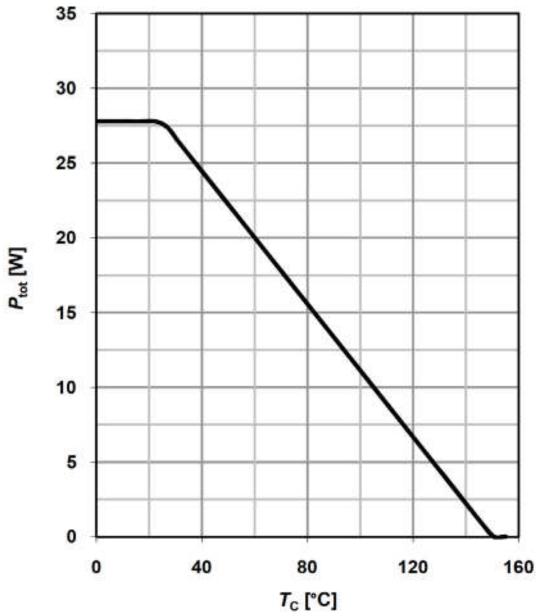
<table>
<tr><th>Power dissipation
Non FullPAK</th><th>Power dissipation
FullPAK</th></tr>
<tr><td>
</td><td>
</td></tr>
<tr><td>$P_{tot} = f(T_C)$</td><td>$P_{tot} = f(T_C)$</td></tr>
</table>

Table 11

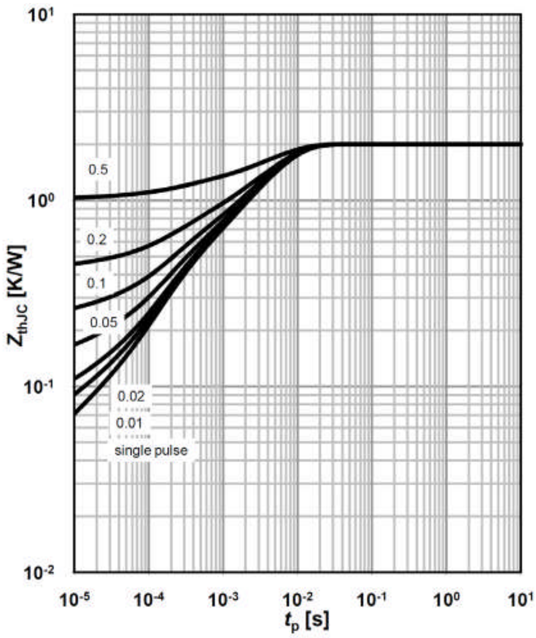
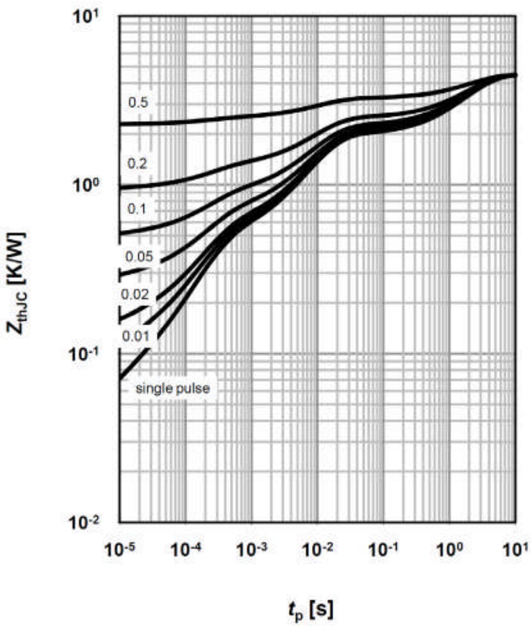
<table>
<tr><th>Max. transient thermal impedance
Non FullPAK</th><th>Max. transient thermal impedance
FullPAK</th></tr>
<tr><td>
</td><td>
</td></tr>
<tr><td>$Z_{(thJC)}$=f(tp); parameter: D=t_p/T</td><td>$Z_{(thJC)}$=f(tp); parameter: D=t_p/T</td></tr>
</table>

Table 12

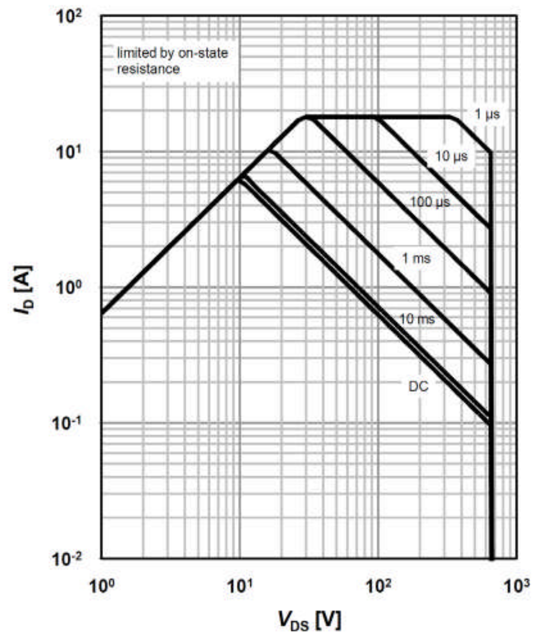
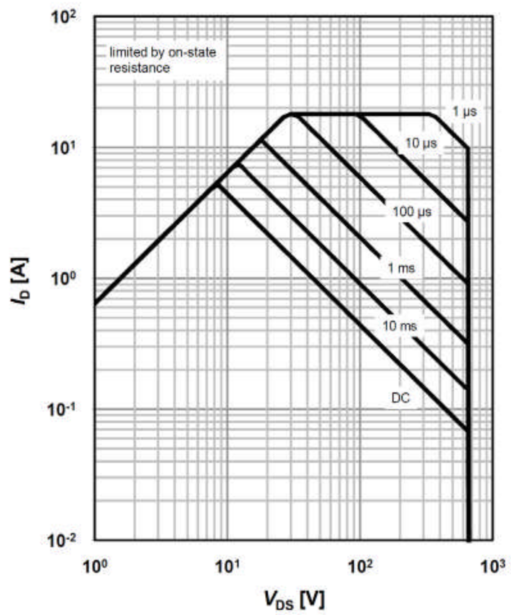
Safe operating area T_C=25 °C **Non FullPAK**	**Safe operating area T_C=25 °C** **FullPAK**
	
I_D=f(V_{DS}); T_C=25 °C; V_{GS} > 7V; D=0; parameter t_p	I_D=f(V_{DS}); T_C=25 °C; V_{GS} > 7V; D=0; parameter t_p

Table 13

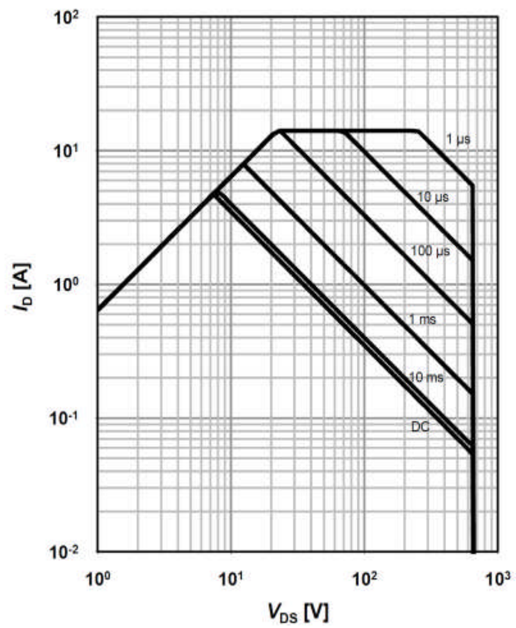
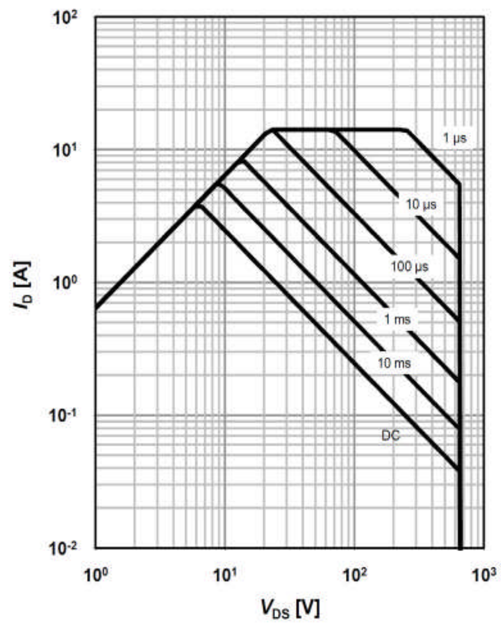
Safe operating area T_C=80 °C **Non FullPAK**	**Safe operating area T_C=80 °C** **FullPAK**
	
I_D=f(V_{DS}); T_C=80 °C; V_{GS} > 7V; D=0; parameter t_p	I_D=f(V_{DS}); T_C=80 °C; V_{GS} > 7V; D=0; parameter t_p

Table 14

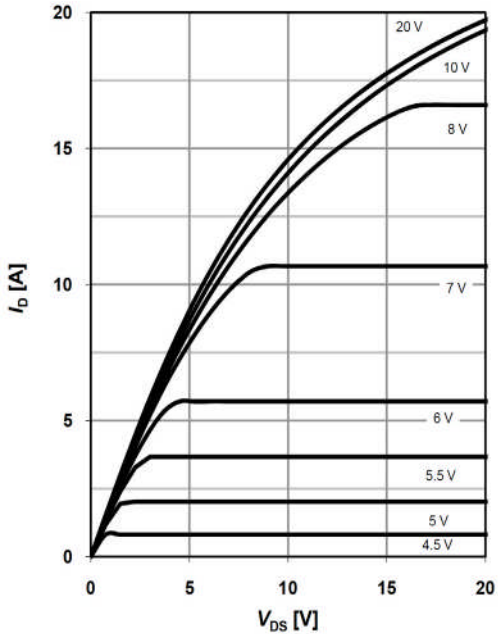
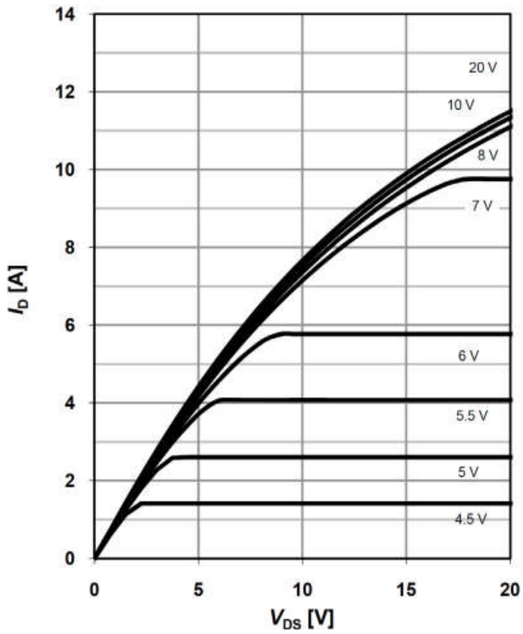
Typ. output characteristics T_C=25 °C	Typ. output characteristics T_j=125 °C
	
I_D=f(V_{DS}); T_j=25 °C; parameter: V_{GS}	I_D=f(V_{DS}); T_j=125 °C; parameter: V_{GS}

Table 15

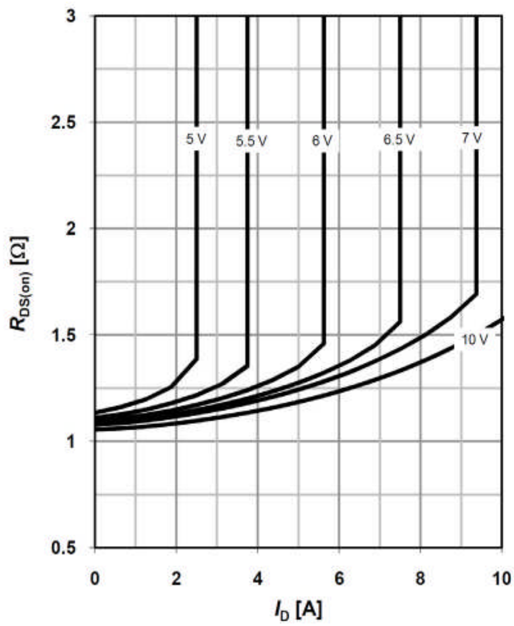
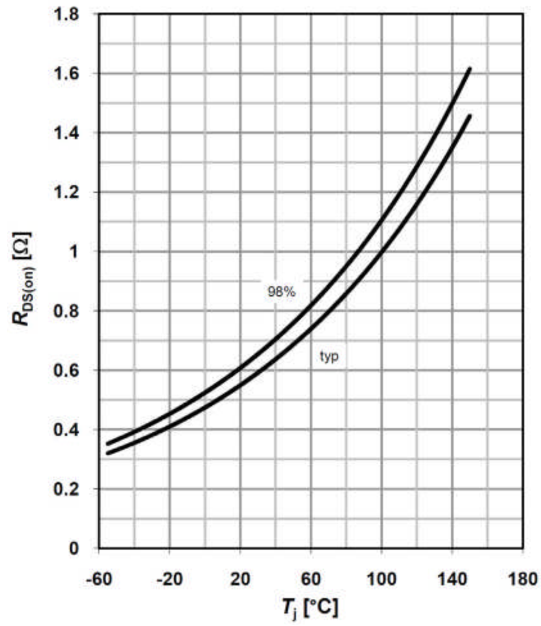
Typ. drain-source on-state resistance	Drain-source on-state resistance
	
$R_{DS(on)}$=f(I_D); T_j=125 °C; parameter: V_{GS}	$R_{DS(on)}$=f(T_j); I_D=4.9 A; V_{GS}=10 V

Table 16

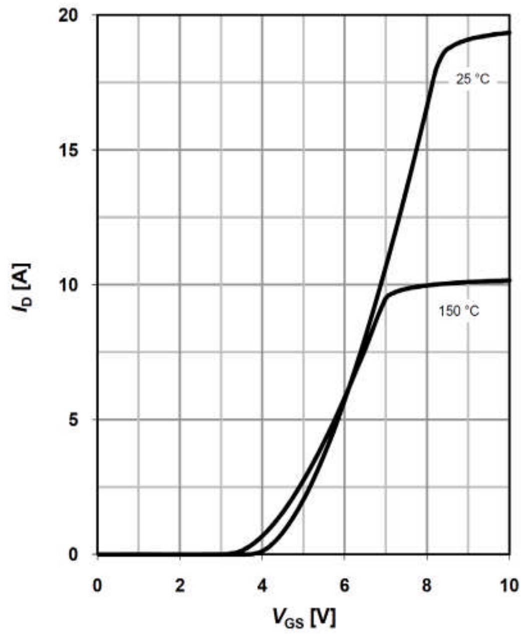
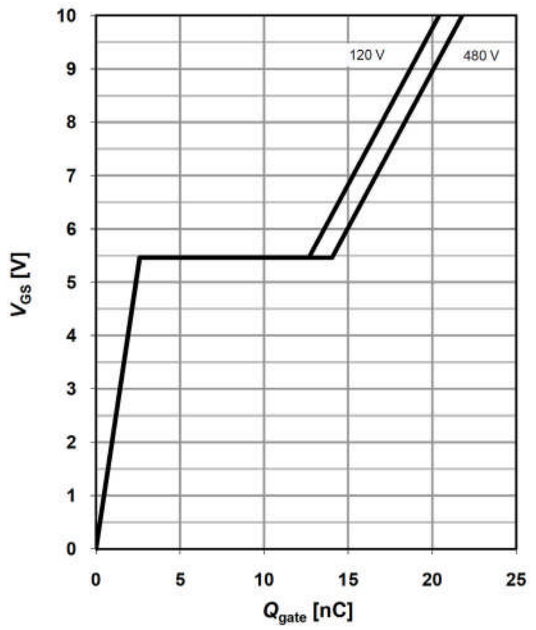
Typ. transfer characteristics	Typ. gate charge
	
I_D=f(V_{GS}); V_{DS}=20V	V_{GS}=f(Q_{gate}), I_D=4.9 A pulsed

Table 17

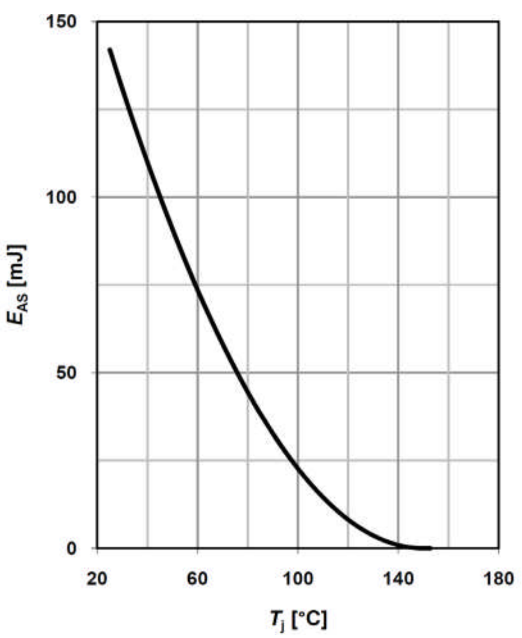
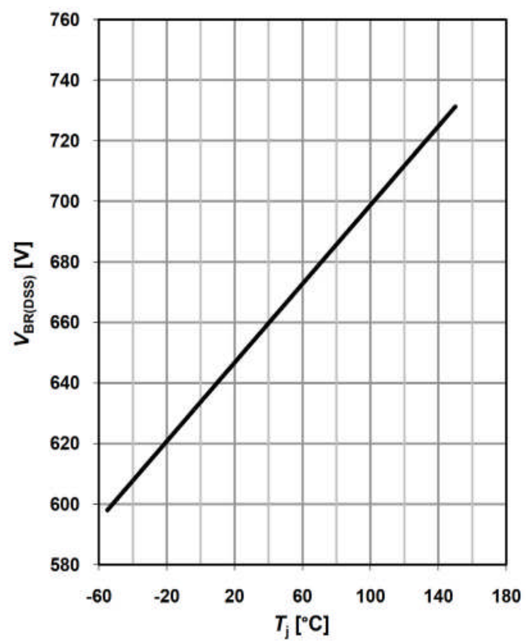
Avalanche energy	Drain-source breakdown voltage
	
E_{AS}=f(T_j); I_D=1.8 A; V_{DD}=50 V	$V_{BR(DSS)}$=f(T_j); I_D=1.0 mA

Table 18

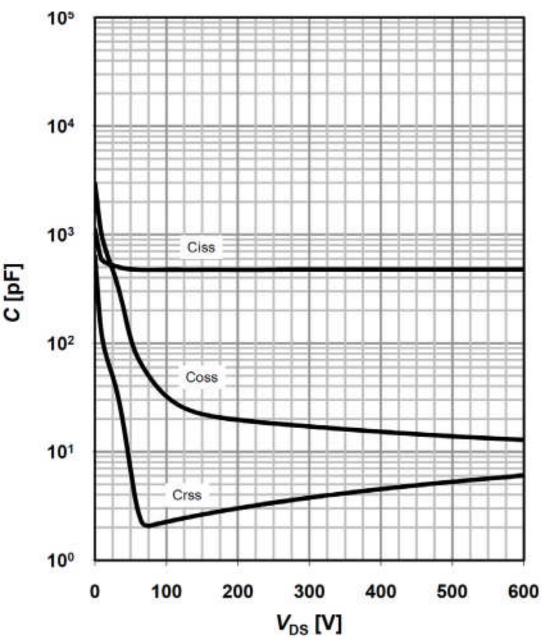
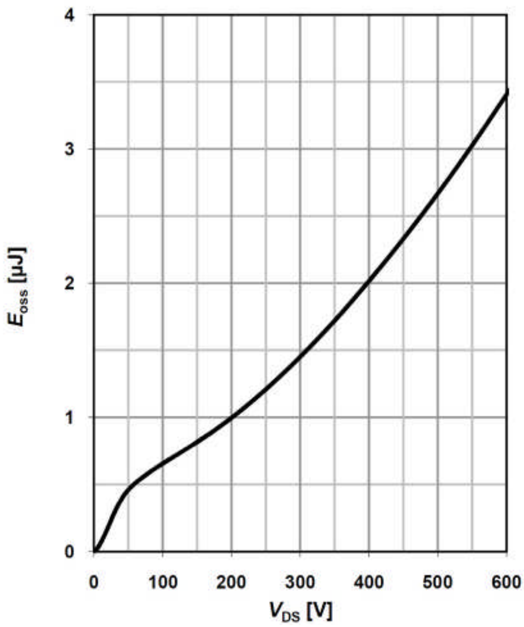
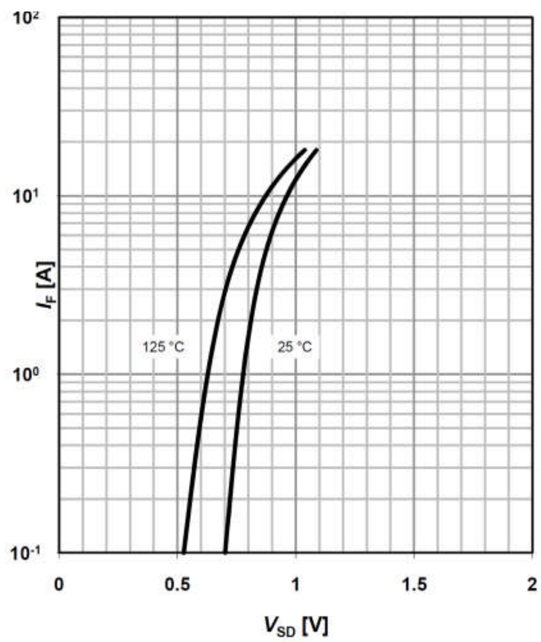
Typ. capacitances	Typ. C_{oss} stored energy
	
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz	E_{oss}=f(V_{DS})

Table 19

Forward characteristics of reverse diode

I_F=f(V_{SD}); parameter: T_j

6 Test circuits

Table 20 Switching times test circuit and waveform for inductive load

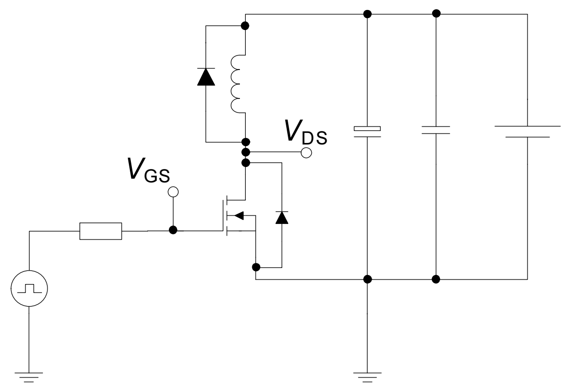
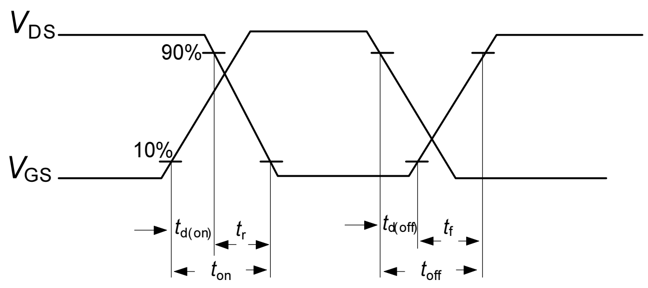
<table>
<tr><th>Switching times test circuit for inductive load</th><th>Switching time waveform</th></tr>
<tr><td>
</td><td>
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Table 21 Unclamped inductive load test circuit and waveform

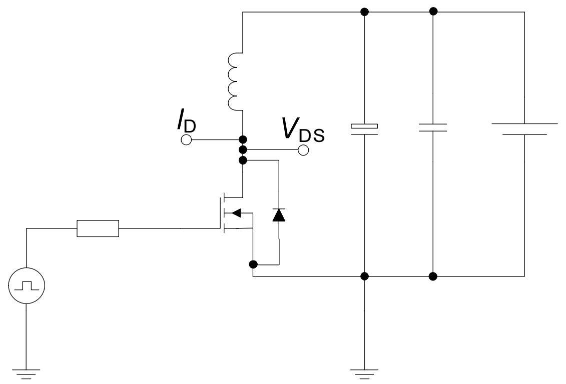
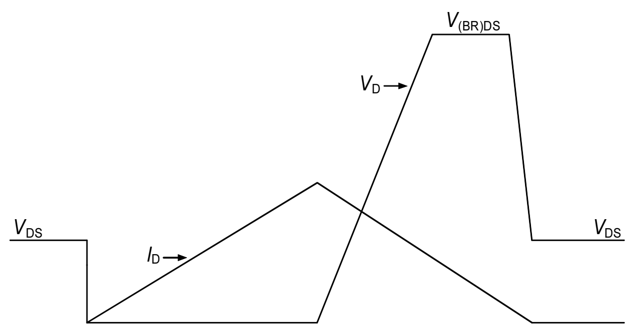
<table>
<tr><th>Unclamped inductive load test circuit</th><th>Unclamped inductive waveform</th></tr>
<tr><td>
</td><td>
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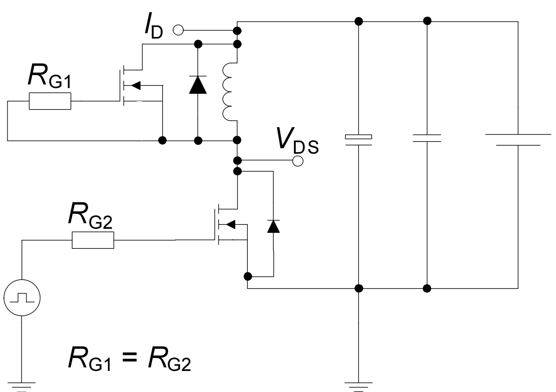
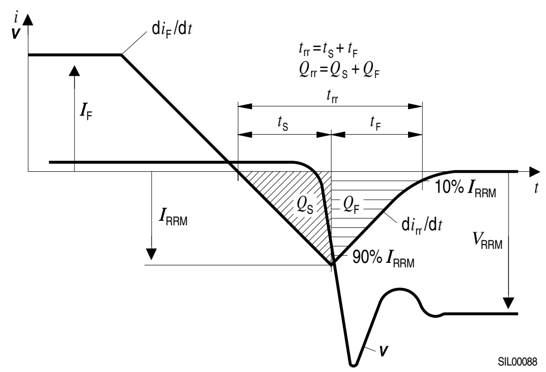
Table 22 Test circuit and waveform for diode characteristics

<table>
<tr><th>Test circuit for diode characteristics</th><th>Diode recovery waveform</th></tr>
<tr><td>
</td><td>
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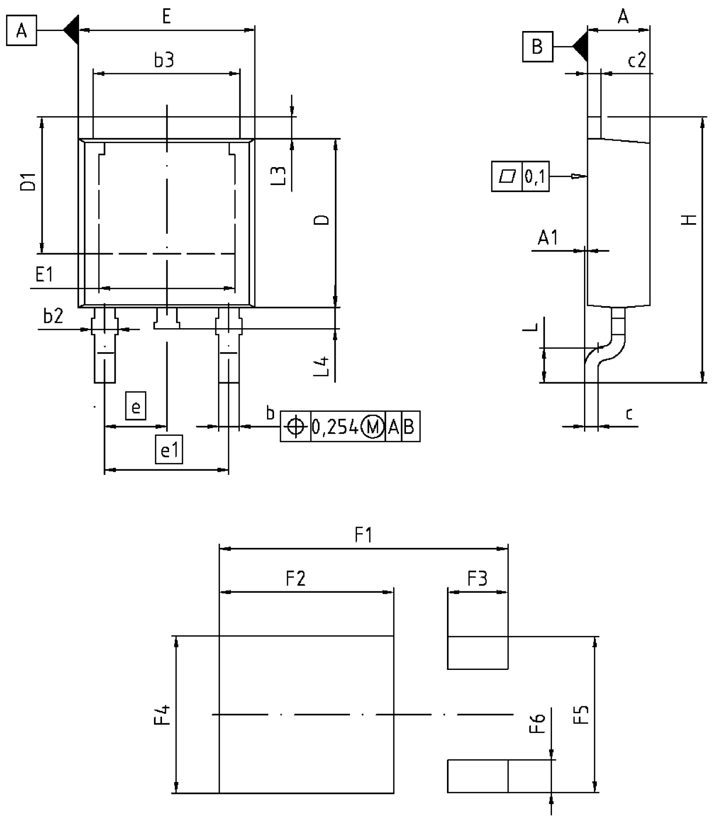
7 Package outlines

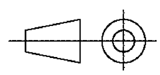


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.50	10.70	0.413	0.421
F2	6.30	6.50	0.248	0.256
F3	2.10	2.30	0.083	0.091
F4	5.70	5.90	0.224	0.232
F5	5.66	5.86	0.223	0.231
F6	1.10	1.30	0.043	0.051

DOCUMENT NO.
Z8B00003328

SCALE 0 2.0 4mm

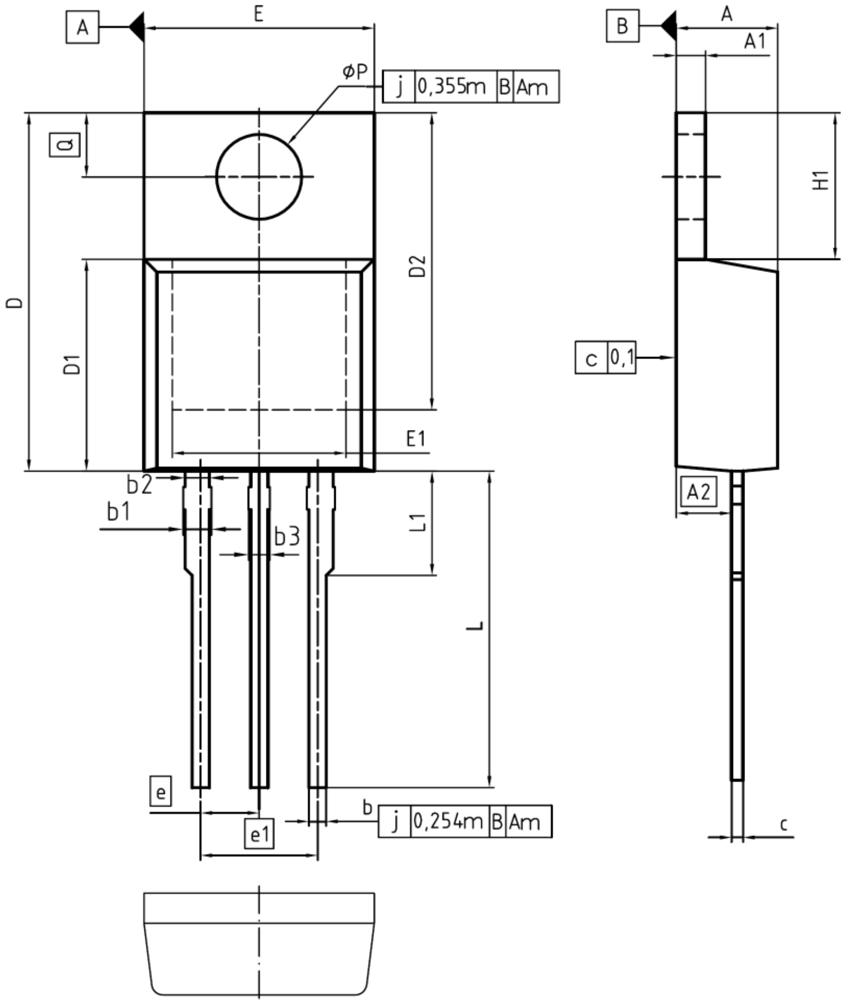
EUROPEAN PROJECTION



ISSUE DATE
19-10-2007

REVISION
03

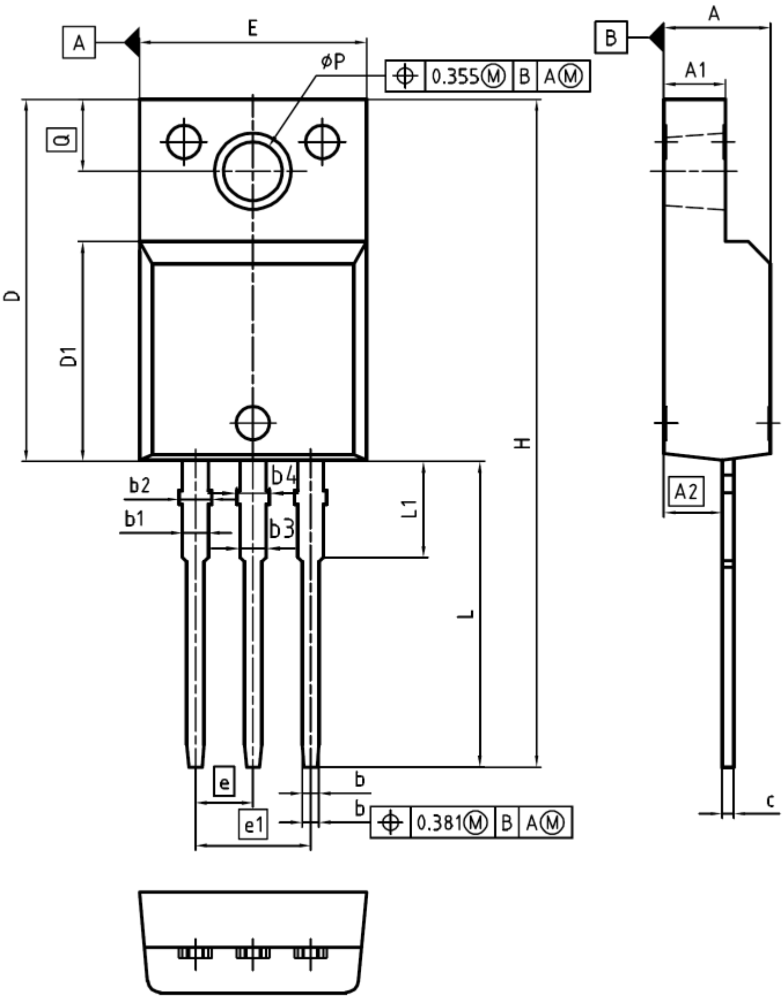
Figure 1 Outlines TO-252, dimensions in mm/inches



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

DOCUMENT NO. Z8B00003318
SCALE 0 2.5 5mm
EUROPEAN PROJECTION
ISSUE DATE 23-08-2007
REVISION 05

Figure 2 Outlines TO-220, dimensions in mm/inches



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
øP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

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SCALE 0 2.5 5mm

EUROPEAN PROJECTION

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03

Figure 3 Outlines TO-220 FullPAK, dimensions in mm/inches

8 Revision History

Revision History: 2010-07-15, Rev. 2.0	
Previous Revision:	
Revision	**Subjects (major changes since last revision)**
2.0	Release of final data sheet

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